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	Applicant NAKAMURA et al.		
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U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
MJ	6,153,008	11/28/2000	Von Ammon et al.	—	—	—

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Name of Patentee	Class	Subclass	Translation	
						Yes	No
MJ	WO 98/45508	10/15/1998	MEMC Electronic Materials, Inc.	—	—	X	
MJ	WO 98/45508	10/15/1998	MEMC Electronic Materials, Inc.	—	—	X	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

MJ	NAKAMURA, KOZO et al.: "Formation process of grown-in defects in Czochralski grown silicon crystals" JOURNAL OF CRYSTAL GROWTH 180 (1997) 61-72
MJ	AMMON, WILFRIED VON et al.: "The dependence of bulk defects on the axial temperature gradient of silicon crystals during Czochralski growth" 2300 JOURNAL OF CRYSTAL GROWTH 151 (1995) June I, Nos. 3/4, Amsterdam, NL, Pages 273-277

Examiner <i>MJA</i>	Date Considered 5/9/2002
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*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.